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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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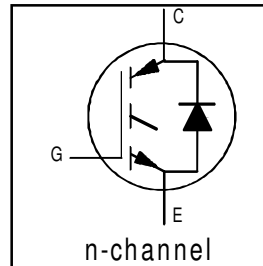
IRG4IBC20KD

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

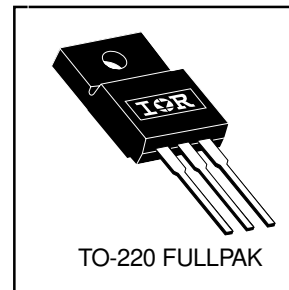
- High switching speed optimized for up to 25kHz with low $V_{CE(on)}$
- Short Circuit Rating 10 μ s @ 125°C, $V_{GE} = 15V$
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than previous generation
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220 FULLPAK



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 2.27V$
@ $V_{GE} = 15V, I_C = 6.3A$

Benefits

- Generation 4 IGBTs offer highest efficiencies available maximizing the power density of the system
- IGBTs optimized for specific application conditions
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise EMI
- Designed to exceed the power handling capability of equivalent industry-standard IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	11.5	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.3	
I_{CM}	Pulsed Collector Current ①	23	
I_{LM}	Clamped Inductive Load Current ②	24	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	6.3	
I_{FM}	Diode Maximum Forward Current	24	
t_{sc}	Short Circuit Withstand Time	10	μ s
V_{ISOL}	RMS Isolation Voltage, Terminal to Case, t = 1 min	2500	V
V_{GE}	Gate-to-Emitter Voltage	± 20	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	34	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	14	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	3.7	$^\circ C/W$
$R_{\theta CS}$	Junction-to-Case - Diode	—	5.5	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	65	
Wt	Weight	2.0 (0.07)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.49	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.27	2.8	V	$I_C = 9.0A$ $I_C = 16A$ $I_C = 9.0A, T_J = 150^\circ\text{C}$
		—	3.01	—		
		—	2.43	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ^④	2.9	4.3	—	S	$V_{CE} = 100V, I_C = 9.0A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
		—	—	1000		
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 8.0A$ $I_C = 8.0A, T_J = 150^\circ\text{C}$
		—	1.3	1.6		
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	34	51	nC	$I_C = 9.0A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8
Q_{ge}	Gate - Emitter Charge (turn-on)	—	4.9	7.4		
Q_{gc}	Gate - Collector Charge (turn-on)	—	14	21		
$t_{d(on)}$	Turn-On Delay Time	—	54	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 9.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$
t_r	Rise Time	—	34	—		
$t_{d(off)}$	Turn-Off Delay Time	—	180	270		
t_f	Fall Time	—	72	110		
E_{on}	Turn-On Switching Loss	—	0.34	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.30	—		
E_{ts}	Total Switching Loss	—	0.64	0.96		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 50\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	51	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 9.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ See Fig. 10,11,14 Energy losses include "tail" and diode reverse recovery
t_r	Rise Time	—	37	—		
$t_{d(off)}$	Turn-Off Delay Time	—	220	—		
t_f	Fall Time	—	160	—		
E_{ts}	Total Switching Loss	—	0.85	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	450	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
C_{oes}	Output Capacitance	—	61	—		
C_{res}	Reverse Transfer Capacitance	—	14	—		
t_{rr}	Diode Reverse Recovery Time	—	37	55	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$
		—	55	90		
I_{rr}	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$
		—	4.5	8.0		
Q_{rr}	Diode Reverse Recovery Charge	—	65	138	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$
		—	124	360		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	240	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$
		—	210	—		

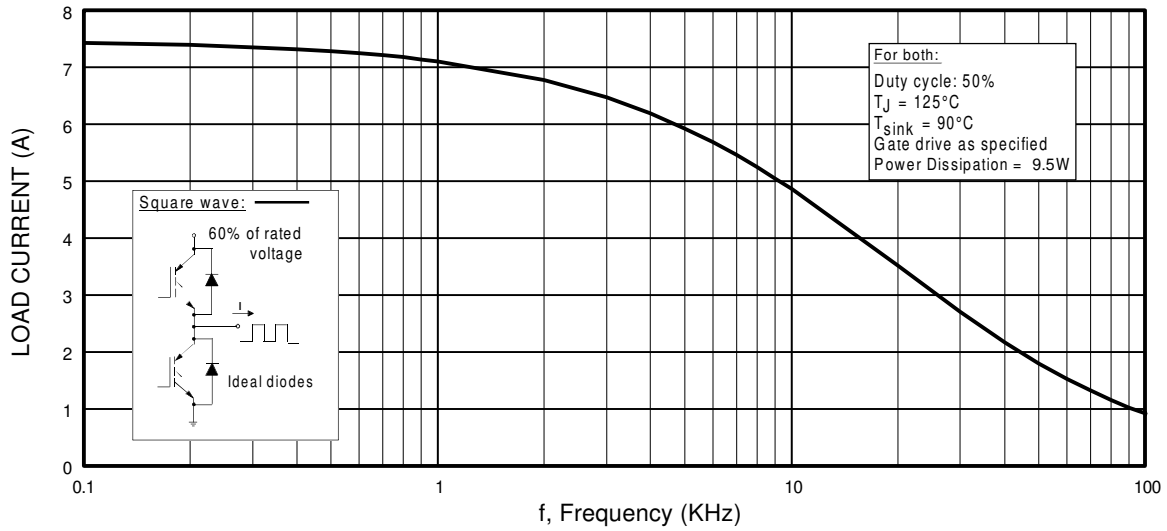


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

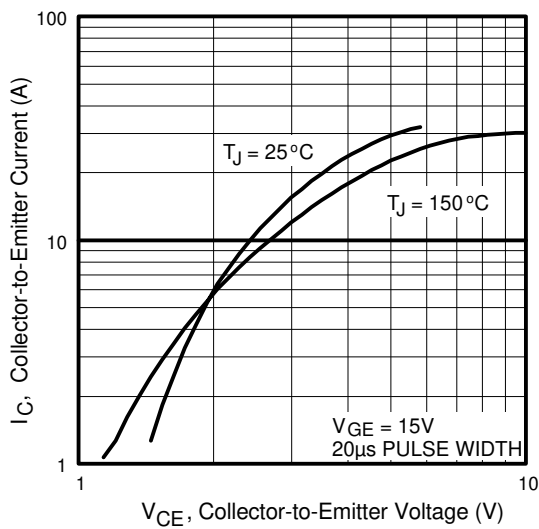


Fig. 2 - Typical Output Characteristics

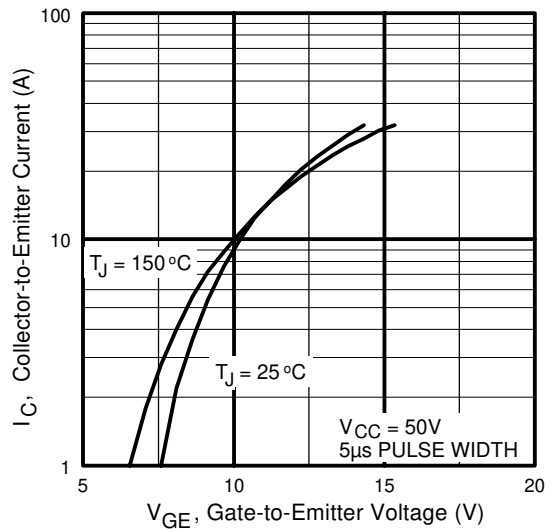


Fig. 3 - Typical Transfer Characteristics

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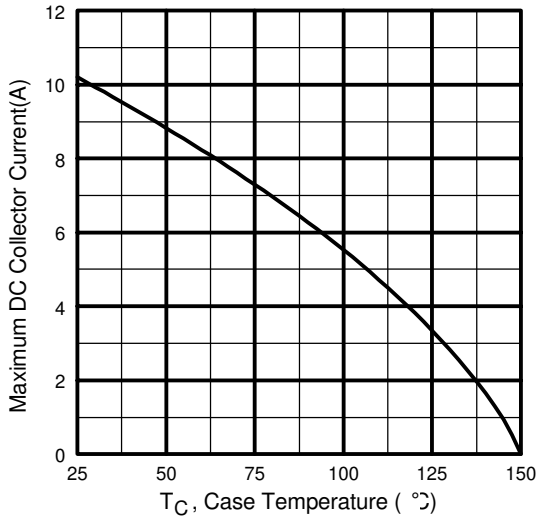


Fig. 4 - Maximum Collector Current vs. Case Temperature

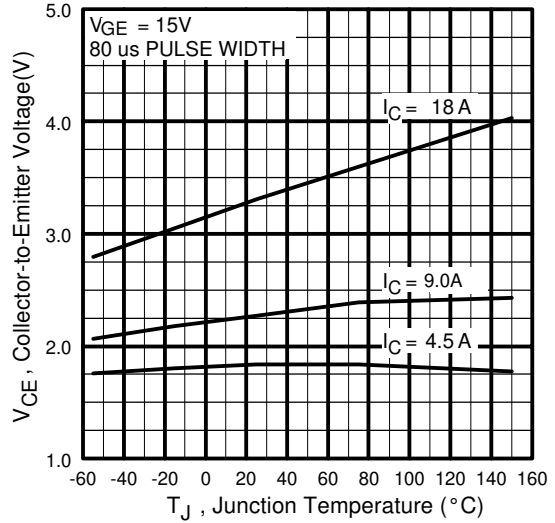


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

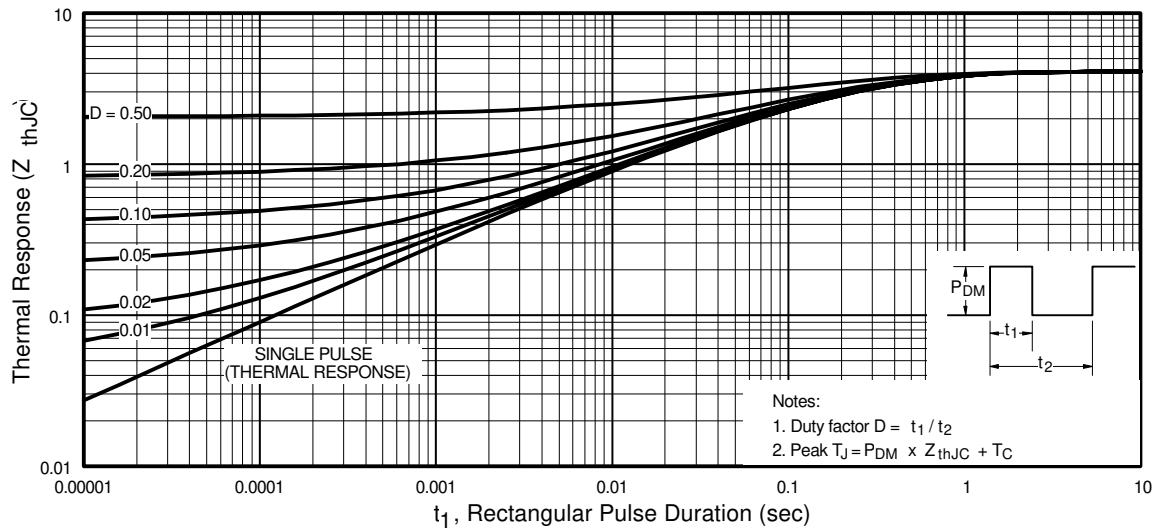


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

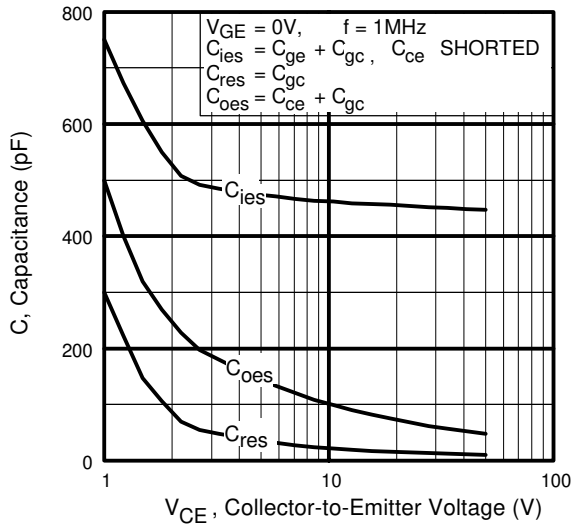


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

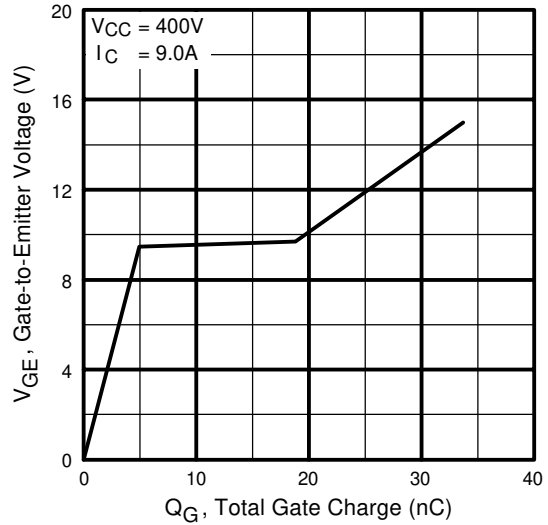


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

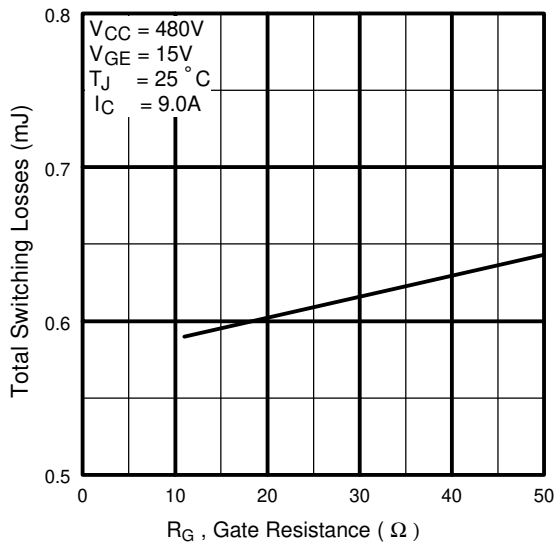


Fig. 9 - Typical Switching Losses vs. Gate Resistance

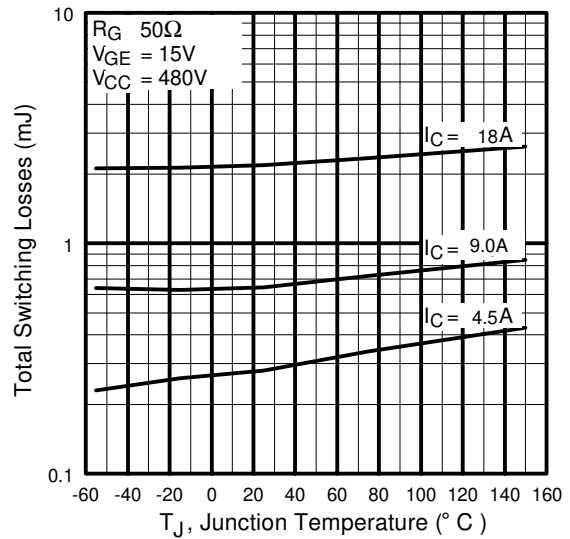


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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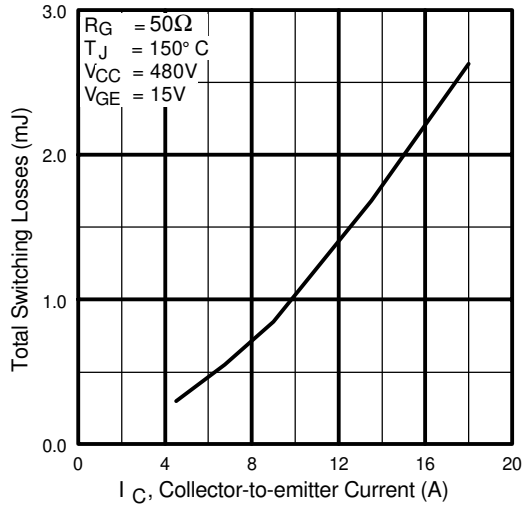


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

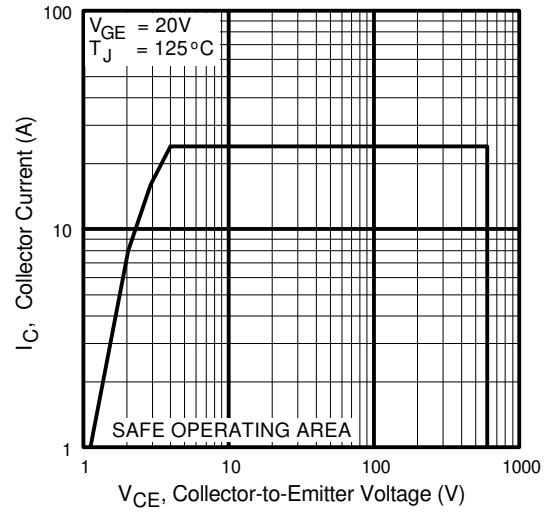


Fig. 12 - Turn-Off SOA

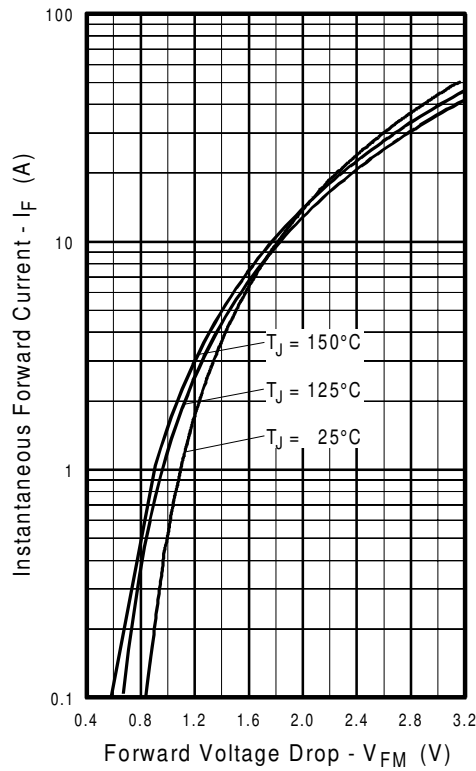


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

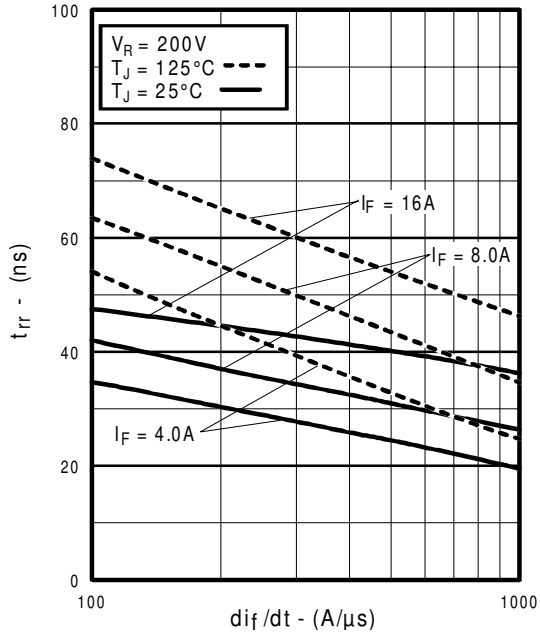


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

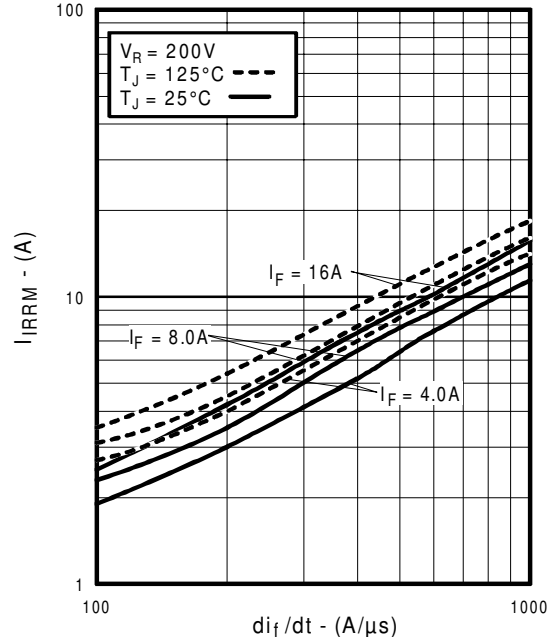


Fig. 15 - Typical Recovery Current vs. di_f/dt

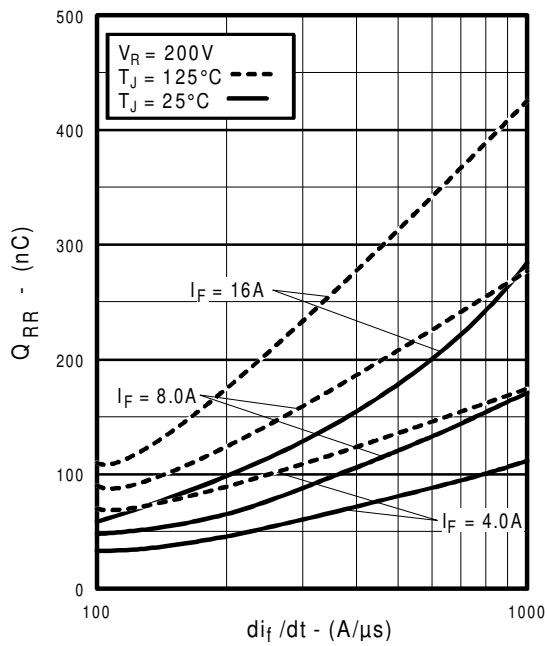


Fig. 16 - Typical Stored Charge vs. di_f/dt

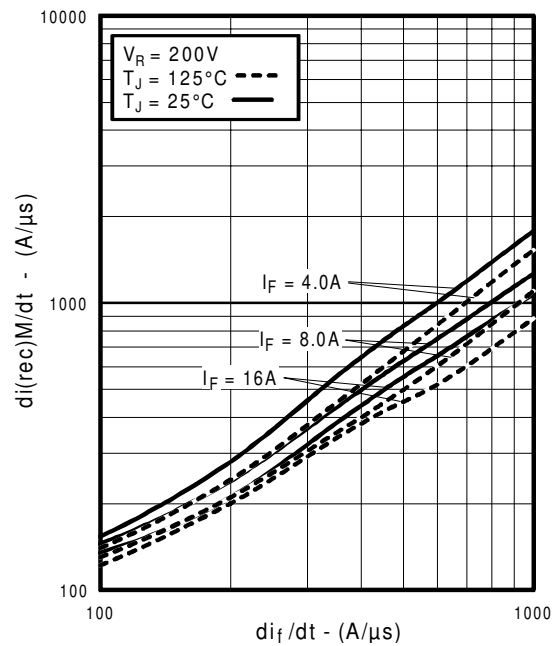


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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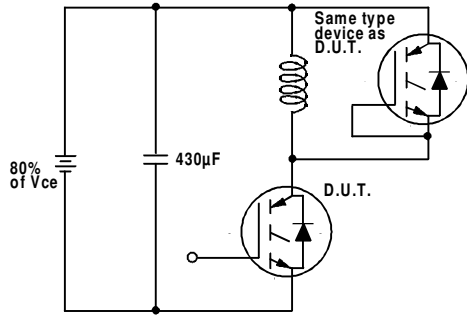


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

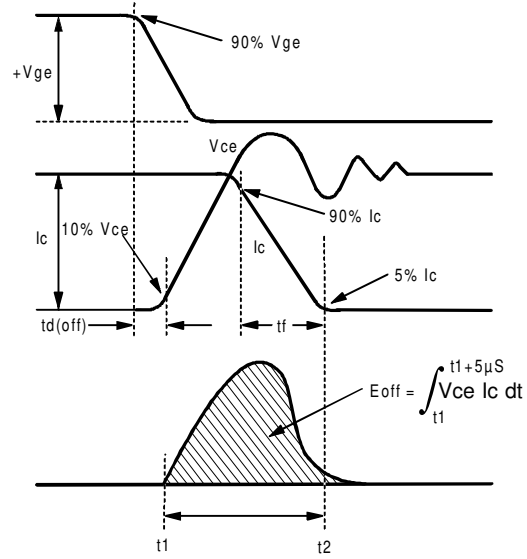


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

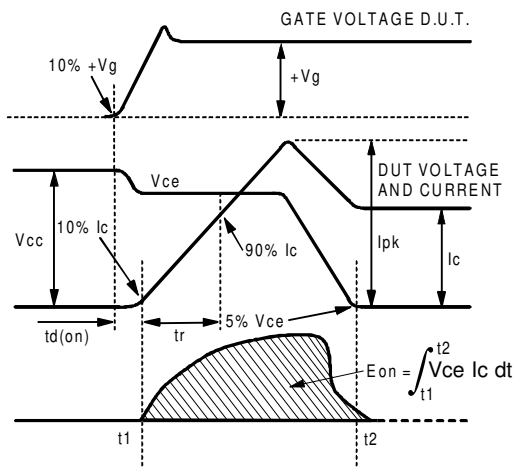


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

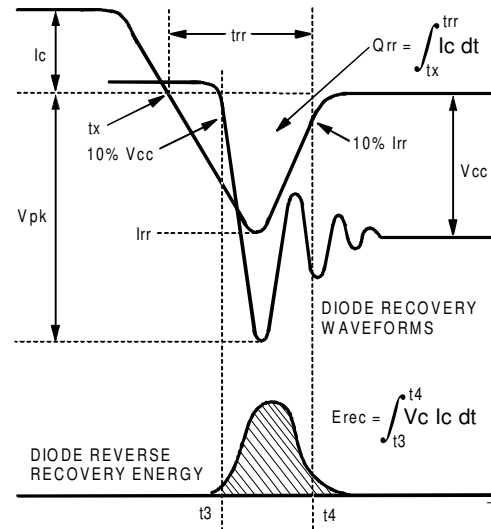


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

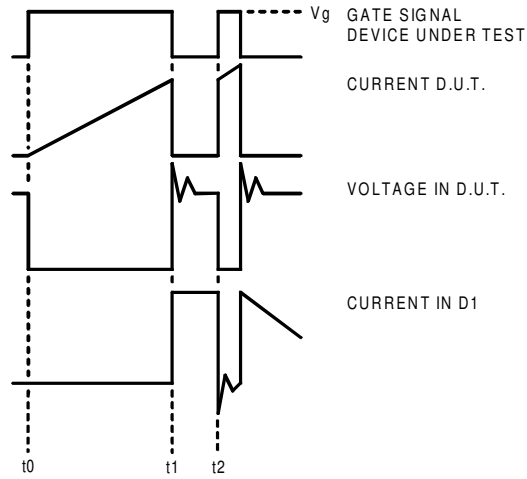


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

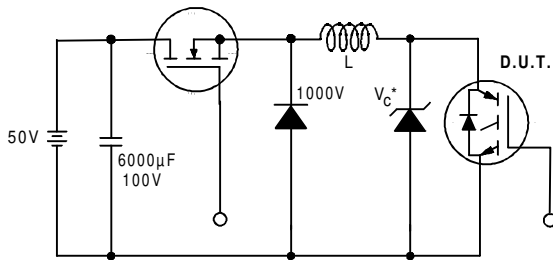


Figure 19. Clamped Inductive Load Test Circuit

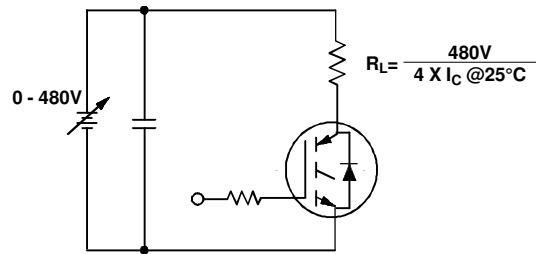


Figure 20. Pulsed Collector Current Test Circuit

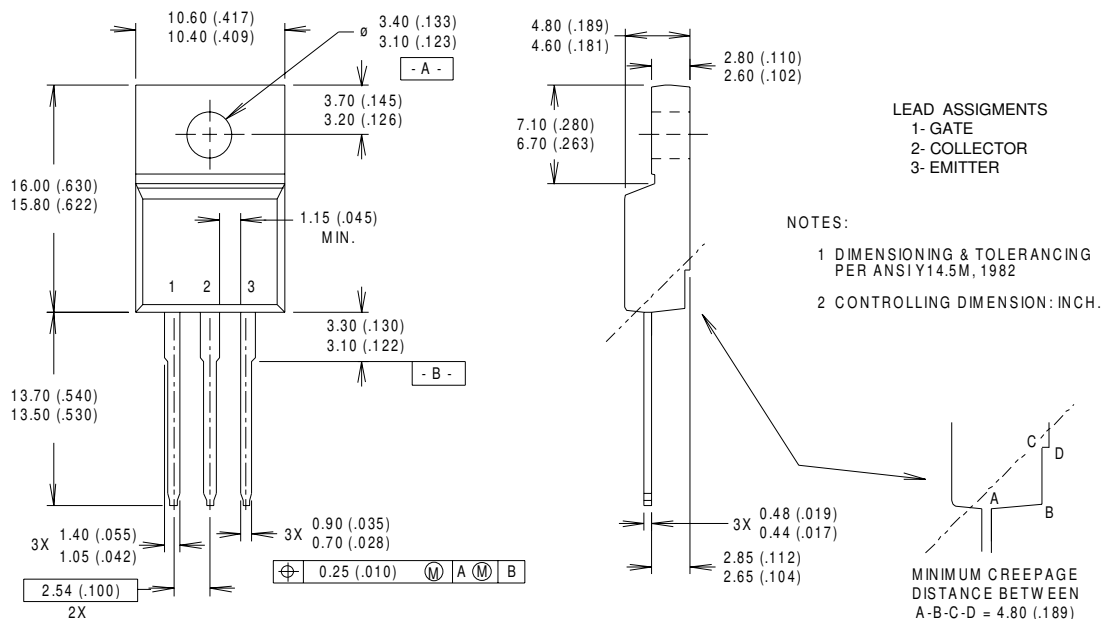
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International
IR Rectifier

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

Case Outline — TO-220 FULLPAK



International
IR Rectifier

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Data and specifications subject to change without notice. 10/00

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>